MRAM ARRAY HAVING A SEGMENTED BIT LINE

ABSTRACT

A magneto-resistive random access memory (MRAM) array comprises global bit lines segmented using a plurality of local bit lines. A read/write controller is connected to the switches. Switches couple the global bit line to the local bit lines. The MRAM array has low leakage currents and facilitates a high signal-to-noise (S/N) ratio of read and write operations.